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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I²C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	77
Program Memory Size	1MB (1M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	80K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 7x10b, 5x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	100-LQFP
Supplier Device Package	100-LQFP (14x14)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5606bk0vll6

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function[1]	Function	Peripheral	I/O direction	Pad type[2]	RESET config.[3]	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PD[13]	PCR[61]	AF0 AF1 AF2 AF3 —	GPIO[61] CS0_1 E0UC[25] — ADC0_S[5]	SIUL DSPI_1 eMIOS_0 — ADC_0	I/O I/O I/O — I	J	Tristate	62	84	102
PD[14]	PCR[62]	AF0 AF1 AF2 AF3 —	GPIO[62] CS1_1 E0UC[26] — ADC0_S[6]	SIUL DSPI_1 eMIOS_0 — ADC_0	I/O O I/O — I	J	Tristate	64	86	104
PD[15]	PCR[63]	AF0 AF1 AF2 AF3 —	GPIO[63] CS2_1 E0UC[27] — ADC0_S[7]	SIUL DSPI_1 eMIOS_0 — ADC_0	I/O O I/O — I	J	Tristate	66	88	106
Port E										
PE[0]	PCR[64]	AF0 AF1 AF2 AF3 — —	GPIO[64] E0UC[16] — — WKUP[6][4] CAN5RX	SIUL eMIOS_0 — — WKUP FlexCAN_5	I/O I/O — — I I	S	Tristate	6	10	18
PE[1]	PCR[65]	AF0 AF1 AF2 AF3	GPIO[65] E0UC[17] CAN5TX —	SIUL eMIOS_0 FlexCAN_5 —	I/O I/O O —	M	Tristate	8	12	20
PE[2]	PCR[66]	AF0 AF1 AF2 AF3 — —	GPIO[66] E0UC[18] — — EIRQ[21] SIN_1	SIUL eMIOS_0 — — SIUL DSPI_1	I/O I/O — — I I	M	Tristate	89	128	156
PE[3]	PCR[67]	AF0 AF1 AF2 AF3	GPIO[67] E0UC[19] SOUT_1 —	SIUL eMIOS_0 DSPI_1 —	I/O I/O O —	M	Tristate	90	129	157
PE[4]	PCR[68]	AF0 AF1 AF2 AF3 —	GPIO[68] E0UC[20] SCK_1 — EIRQ[9]	SIUL eMIOS_0 DSPI_1 — SIUL	I/O I/O I/O — I	M	Tristate	93	132	160
PE[5]	PCR[69]	AF0 AF1 AF2 AF3	GPIO[69] E0UC[21] CS0_1 MA[2]	SIUL eMIOS_0 DSPI_1 ADC_0	I/O I/O I/O O	M	Tristate	94	133	161

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function[1]	Function	Peripheral	I/O direction	Pad type[2]	RESET config.[3]	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PE[6]	PCR[70]	AF0 AF1 AF2 AF3 —	GPIO[70] E0UC[22] CS3_0 MA[1] EIRQ[22]	SIUL eMIOS_0 DSPI_0 ADC_0 SIUL	I/O I/O O O I	M	Tristate	95	139	167
PE[7]	PCR[71]	AF0 AF1 AF2 AF3 —	GPIO[71] E0UC[23] CS2_0 MA[0] EIRQ[23]	SIUL eMIOS_0 DSPI_0 ADC_0 SIUL	I/O I/O O O I	M	Tristate	96	140	168
PE[8]	PCR[72]	AF0 AF1 AF2 AF3	GPIO[72] CAN2TX E0UC[22] CAN3TX	SIUL FlexCAN_2 eMIOS_0 FlexCAN_3	I/O O I/O O	M	Tristate	9	13	21
PE[9]	PCR[73]	AF0 AF1 AF2 AF3 — — —	GPIO[73] — E0UC[23] — WKUP[7][4] CAN2RX CAN3RX	SIUL — eMIOS_0 — WKUP FlexCAN_2 FlexCAN_3	I/O — I/O — I I I	S	Tristate	10	14	22
PE[10]	PCR[74]	AF0 AF1 AF2 AF3 —	GPIO[74] LIN3TX CS3_1 E1UC[30] EIRQ[10]	SIUL LINFlex_3 DSPI_1 eMIOS_1 SIUL	I/O O O I/O I	S	Tristate	11	15	23
PE[11]	PCR[75]	AF0 AF1 AF2 AF3 — —	GPIO[75] E0UC[24] CS4_1 — LIN3RX WKUP[14][4]	SIUL eMIOS_0 DSPI_1 — LINFlex_3 WKUP	I/O I/O O — I I	S	Tristate	13	17	25
PE[12]	PCR[76]	AF0 AF1 AF2 AF3 — — —	GPIO[76] — E1UC[19][10] — EIRQ[11] SIN_2 ADC1_S[7]	SIUL — eMIOS_1 — SIUL DSPI_2 ADC_1	I/O — I/O — I I I	J	Tristate	76	109	133
PE[13]	PCR[77]	AF0 AF1 AF2 AF3	GPIO[77] SOUT_2 E1UC[20] —	SIUL DSPI_2 eMIOS_1 —	I/O O I/O —	S	Tristate	—	103	127

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function[1]	Function	Peripheral	I/O direction	Pad type[2]	RESET config.[3]	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PF[7]	PCR[87]	AF0 AF1 AF2 AF3 —	GPIO[87] — CS2_1 — ADC0_S[15]	SIUL — DSPI_1 — ADC_0	I/O — O — I	J	Tristate	—	62	70
PF[8]	PCR[88]	AF0 AF1 AF2 AF3	GPIO[88] CAN3TX CS4_0 CAN2TX	SIUL FlexCAN_3 DSPI_0 FlexCAN_2	I/O O O O	M	Tristate	—	34	42
PF[9]	PCR[89]	AF0 AF1 AF2 AF3 — — —	GPIO[89] E1UC[1] CS5_0 — WKUP[22][4] CAN2RX CAN3RX	SIUL eMIOS_1 DSPI_0 — WKUP FlexCAN_2 FlexCAN_3	I/O I/O O — I I I	S	Tristate	—	33	41
PF[10]	PCR[90]	AF0 AF1 AF2 AF3	GPIO[90] CS1_0 LIN4TX E1UC[2]	SIUL DSPI_0 LINFlex_4 eMIOS_1	I/O O O I/O	M	Tristate	—	38	46
PF[11]	PCR[91]	AF0 AF1 AF2 AF3 — —	GPIO[91] CS2_0 E1UC[3] — WKUP[15][4] LIN4RX	SIUL DSPI_0 eMIOS_1 — WKUP LINFlex_4	I/O O I/O — I I	S	Tristate	—	39	47
PF[12]	PCR[92]	AF0 AF1 AF2 AF3	GPIO[92] E1UC[25] LIN5TX —	SIUL eMIOS_1 LINFlex_5 —	I/O I/O O —	M	Tristate	—	35	43
PF[13]	PCR[93]	AF0 AF1 AF2 AF3 — —	GPIO[93] E1UC[26] — — WKUP[16][4] LIN5RX	SIUL eMIOS_1 — — WKUP LINFlex_5	I/O I/O — — I I	S	Tristate	—	41	49
PF[14]	PCR[94]	AF0 AF1 AF2 AF3	GPIO[94] CAN4TX E1UC[27] CAN1TX	SIUL FlexCAN_4 eMIOS_1 FlexCAN_1	I/O O I/O O	M	Tristate	—	102	126

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function[1]	Function	Peripheral	I/O direction	Pad type[2]	RESET config.[3]	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PH[0]	PCR[112]	AF0 AF1 AF2 AF3 —	GPIO[112] E1UC[2] — — SIN_1	SIUL eMIOS_1 — — DSPI_1	I/O I/O — — I	M	Tristate	—	93	117
PH[1]	PCR[113]	AF0 AF1 AF2 AF3	GPIO[113] E1UC[3] SOUT_1 —	SIUL eMIOS_1 DSPI_1 —	I/O I/O O —	M	Tristate	—	94	118
PH[2]	PCR[114]	AF0 AF1 AF2 AF3	GPIO[114] E1UC[4] SCK_1 —	SIUL eMIOS_1 DSPI_1 —	I/O I/O I/O —	M	Tristate	—	95	119
PH[3]	PCR[115]	AF0 AF1 AF2 AF3	GPIO[115] E1UC[5] CS0_1 —	SIUL eMIOS_1 DSPI_1 —	I/O I/O I/O —	M	Tristate	—	96	120
PH[4]	PCR[116]	AF0 AF1 AF2 AF3	GPIO[116] E1UC[6] — —	SIUL eMIOS_1 — —	I/O I/O — —	M	Tristate	—	134	162
PH[5]	PCR[117]	AF0 AF1 AF2 AF3	GPIO[117] E1UC[7] — —	SIUL eMIOS_1 — —	I/O I/O — —	S	Tristate	—	135	163
PH[6]	PCR[118]	AF0 AF1 AF2 AF3	GPIO[118] E1UC[8] — MA[2]	SIUL eMIOS_1 — ADC_0	I/O I/O — O	M	Tristate	—	136	164
PH[7]	PCR[119]	AF0 AF1 AF2 AF3	GPIO[119] E1UC[9] CS3_2 MA[1]	SIUL eMIOS_1 DSPI_2 ADC_0	I/O I/O O O	M	Tristate	—	137	165
PH[8]	PCR[120]	AF0 AF1 AF2 AF3	GPIO[120] E1UC[10] CS2_2 MA[0]	SIUL eMIOS_1 DSPI_2 ADC_0	I/O I/O O O	M	Tristate	—	138	166
PH[9][8]	PCR[121]	AF0 AF1 AF2 AF3	GPIO[121] — TCK —	SIUL — JTAGC —	I/O — I —	S	Input, weak pull-up	88	127	155
PH[10][8]	PCR[122]	AF0 AF1 AF2 AF3	GPIO[122] — TMS —	SIUL — JTAGC —	I/O — I —	M	Input, weak pull-up	81	120	148

Table 2. Functional port pins (continued)

Port pin	PCR register	Alternate function[1]	Function	Peripheral	I/O direction	Pad type[2]	RESET config.[3]	Pin number		
								100 LQFP	144 LQFP	176 LQFP
PI[14]	PCR[142]	AF0 AF1 AF2 AF3 — —	GPIO[142] — — — ADC0_S[22] SIN_4	SIUL — — — ADC_0 DSPI_4	I/O — — — I I	J	Tristate	—	—	76
PI[15]	PCR[143]	AF0 AF1 AF2 AF3 —	GPIO[143] CS0_4 — — ADC0_S[23]	SIUL DSPI_4 — — ADC_0	I/O I/O — — I	J	Tristate	—	—	75
Port J										
PJ[0]	PCR[144]	AF0 AF1 AF2 AF3 —	GPIO[144] CS1_4 — — ADC0_S[24]	SIUL DSPI_4 — — ADC_0	I/O I/O — — I	J	Tristate	—	—	74
PJ[1]	PCR[145]	AF0 AF1 AF2 AF3 — —	GPIO[145] — — — ADC0_S[25] SIN_5	SIUL — — —— ADC_0 DSPI_5	I/O — — — I I	J	Tristate	—	—	73
PJ[2]	PCR[146]	AF0 AF1 AF2 AF3 —	GPIO[146] CS0_5 — — ADC0_S[26]	SIUL DSPI_5 — — ADC_0	I/O I/O — — I	J	Tristate	—	—	72
PJ[3]	PCR[147]	AF0 AF1 AF2 AF3 —	GPIO[147] CS1_5 — — ADC0_S[27]	SIUL DSPI_5 — — ADC_0	I/O I/O — — I	J	Tristate	—	—	71
PJ[4]	PCR[148]	AF0 AF1 AF2 AF3	GPIO[148] SCK_5 E1UC[18] —	SIUL DSPI_5 eMIOS_1 —	I/O I/O — —	M	Tristate	—	—	5

1 Alternate functions are chosen by setting the values of the PCR.PA bitfields inside the SIUL module. PCR.PA = 00 → AF0; PCR.PA = 01 → AF1; PCR.PA = 10 → AF2; PCR.PA = 11 → AF3. This is intended to select the output functions; to use one of the input functions, the PCR.IBE bit must be written to '1', regardless of the values selected in the PCR.PA bitfields. For this reason, the value corresponding to an input only function is reported as "—".

2 See Table 3.

3 The RESET configuration applies during and after reset.

K is a constant for the particular part, which may be determined from Equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J may be obtained by solving equations 1 and 2 iteratively for any value of T_A.

3.6 I/O pad electrical characteristics

3.6.1 I/O pad types

The device provides four main I/O pad types depending on the associated alternate functions:

- Slow pads — are the most common pads, providing a good compromise between transition time and low electromagnetic emission.
- Medium pads — provide transition fast enough for the serial communication channels with controlled current to reduce electromagnetic emission.
- Fast pads — provide maximum speed. These are used for improved debugging capability.
- Input only pads — are associated with ADC channels and 32 kHz low power external crystal oscillator providing low input leakage.

Medium and Fast pads can use slow configuration to reduce electromagnetic emission, at the cost of reducing AC performance.

3.6.2 I/O input DC characteristics

Table 12 provides input DC electrical characteristics as described in Figure 5.

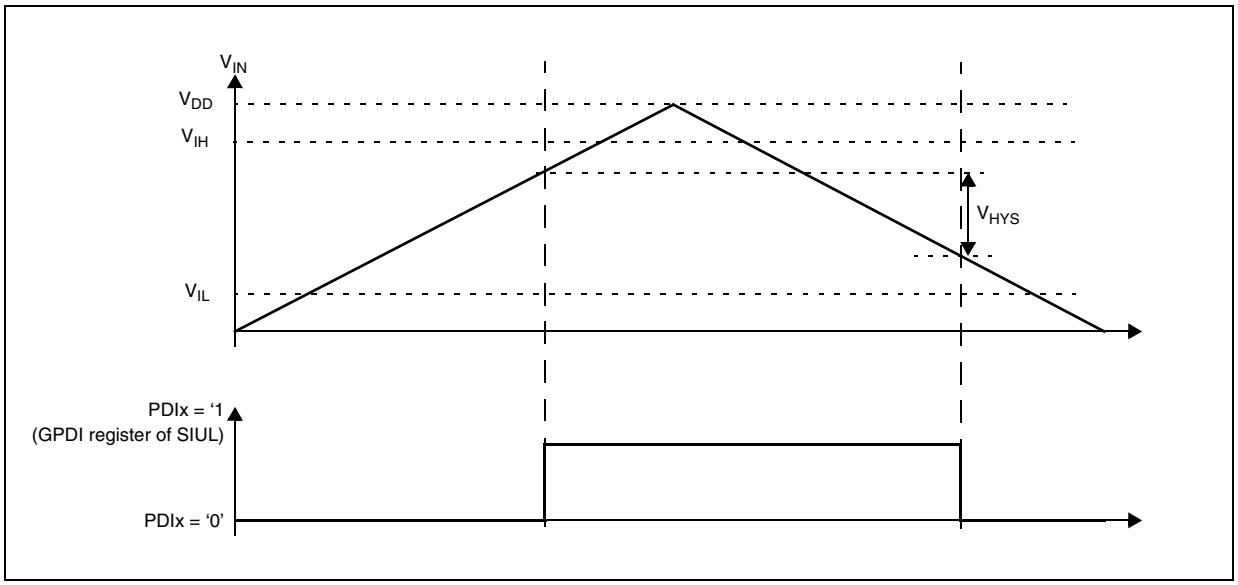


Figure 5. I/O input DC electrical characteristics definition

[2] The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET are configured in input or in high impedance state.

3.6.4 Output pin transition times

Table 17. Output pin transition times

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
T_{tr}	CC	D	Output transition time output pin[2] SLOW configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	50	ns
		T		C_L = 50 pF		—	—	100	
		D		C_L = 100 pF		—	—	125	
		D		C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	50	
		T		C_L = 50 pF		—	—	100	
		D		C_L = 100 pF		—	—	125	
T_{tr}	CC	D	Output transition time output pin[2] MEDIUM configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0 SIUL.PCRx.SRC = 1	—	—	10	ns
		T		C_L = 50 pF		—	—	20	
		D		C_L = 100 pF		—	—	40	
		D		C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1 SIUL.PCRx.SRC = 1	—	—	12	
		T		C_L = 50 pF		—	—	25	
		D		C_L = 100 pF		—	—	40	
T_{tr}	CC	D	Output transition time output pin[2] FAST configuration	C_L = 25 pF	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	4	ns
				C_L = 50 pF		—	—	6	
				C_L = 100 pF		—	—	12	
				C_L = 25 pF	V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	4	
				C_L = 50 pF		—	—	7	
				C_L = 100 pF		—	—	12	

[1] V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

[2] C_L includes device and package capacitances (C_{PKG} < 5 pF).

3.6.5 I/O pad current specification

The I/O pads are distributed across the I/O supply segment. Each I/O supply segment is associated to a V_{DD}/V_{SS} supply pair as described in Table 18.

Table 19 provides I/O consumption figures.

In order to ensure device reliability, the average current of the I/O on a single segment should remain below the I_{AVGSEG} maximum value.

Table 20. I/O weight[1] (continued)

Supply segment			Pad	176 LQFP				144/100 LQFP			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
176 LQFP	144 LQFP	100 LQFP		SRC[2] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
5	3	—	PF[15]	4%	—	4%	—	4%	—	4%	—
		—	PF[14]	4%	6%	5%	5%	4%	6%	5%	5%
		—	PE[13]	4%	—	5%	—	4%	—	5%	—
		3	PA[7]	5%	—	6%	—	5%	—	6%	—
			PA[8]	5%	—	6%	—	5%	—	6%	—
			PA[9]	6%	—	7%	—	6%	—	7%	—
			PA[10]	6%	—	8%	—	6%	—	8%	—
			PA[11]	8%	—	9%	—	8%	—	9%	—
			PE[12]	8%	—	9%	—	8%	—	9%	—
		—	PG[14]	8%	—	9%	—	8%	—	9%	—
		—	PG[15]	8%	11%	9%	10%	8%	11%	9%	10%
		—	PE[14]	8%	—	9%	—	8%	—	9%	—
		—	PE[15]	8%	11%	9%	10%	8%	11%	9%	10%
		—	PG[10]	8%	—	9%	—	8%	—	9%	—
		—	PG[11]	7%	11%	9%	9%	7%	11%	9%	9%
	—	—	PH[11]	7%	10%	9%	9%	—	—	—	—
	—	—	PH[12]	7%	10%	8%	9%	—	—	—	—
	—	—	PI[5]	7%	—	8%	—	—	—	—	—
	—	—	PI[4]	7%	—	8%	—	—	—	—	—
	3	3	PC[3]	6%	—	8%	—	6%	—	8%	—
			PC[2]	6%	8%	7%	7%	6%	8%	7%	7%
			PA[5]	6%	8%	7%	7%	6%	8%	7%	7%
			PA[6]	5%	—	6%	—	5%	—	6%	—
			PH[10]	5%	7%	6%	6%	5%	7%	6%	6%
			PC[1]	5%	19%	5%	13%	5%	19%	5%	13%

Table 20. I/O weight[1] (continued)

Supply segment			Pad	176 LQFP				144/100 LQFP			
				Weight 5 V		Weight 3.3 V		Weight 5 V		Weight 3.3 V	
176 LQFP	144 LQFP	100 LQFP		SRC[2] = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1
6	4	4	PC[0]	6%	9%	7%	8%	7%	10%	8%	8%
			PH[9]	7%	—	8%	—	7%	—	9%	—
			PE[2]	7%	10%	8%	9%	8%	11%	9%	10%
			PE[3]	7%	10%	9%	9%	8%	12%	10%	10%
			PC[5]	7%	11%	9%	9%	8%	12%	10%	11%
			PC[4]	8%	11%	9%	10%	9%	13%	10%	11%
			PE[4]	8%	11%	9%	10%	9%	13%	11%	12%
			PE[5]	8%	11%	10%	10%	9%	14%	11%	12%
		—	PH[4]	8%	12%	10%	10%	10%	14%	12%	12%
		—	PH[5]	8%	—	10%	—	10%	—	12%	—
		—	PH[6]	8%	12%	10%	11%	10%	15%	12%	13%
		—	PH[7]	9%	12%	10%	11%	11%	15%	13%	13%
		—	PH[8]	9%	12%	10%	11%	11%	16%	13%	14%
		4	PE[6]	9%	12%	10%	11%	11%	16%	13%	14%
			PE[7]	9%	12%	10%	11%	11%	16%	14%	14%
	—	—	PI[3]	9%	—	10%	—	—	—	—	—
	—	—	PI[2]	9%	—	10%	—	—	—	—	—
	—	—	PI[1]	9%	—	10%	—	—	—	—	—
	—	—	PI[0]	9%	—	10%	—	—	—	—	—
	4	4	PC[12]	8%	12%	10%	11%	12%	18%	15%	16%
			PC[13]	8%	—	10%	—	13%	—	15%	—
			PC[8]	8%	—	10%	—	13%	—	15%	—
			PB[2]	8%	11%	9%	10%	13%	18%	15%	16%

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 SRC is the Slew Rate Control bit in SIU_PCR*x*

3.7 $\overline{\text{RESET}}$ electrical characteristics

The device implements a dedicated bidirectional $\overline{\text{RESET}}$ pin.

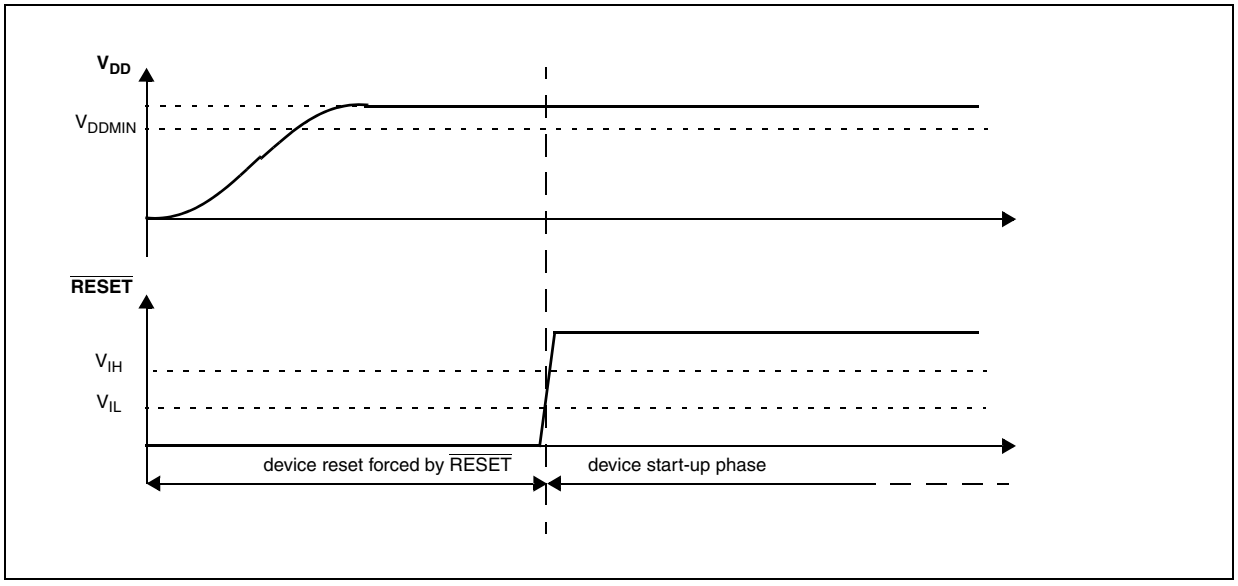


Figure 6. Start-up reset requirements

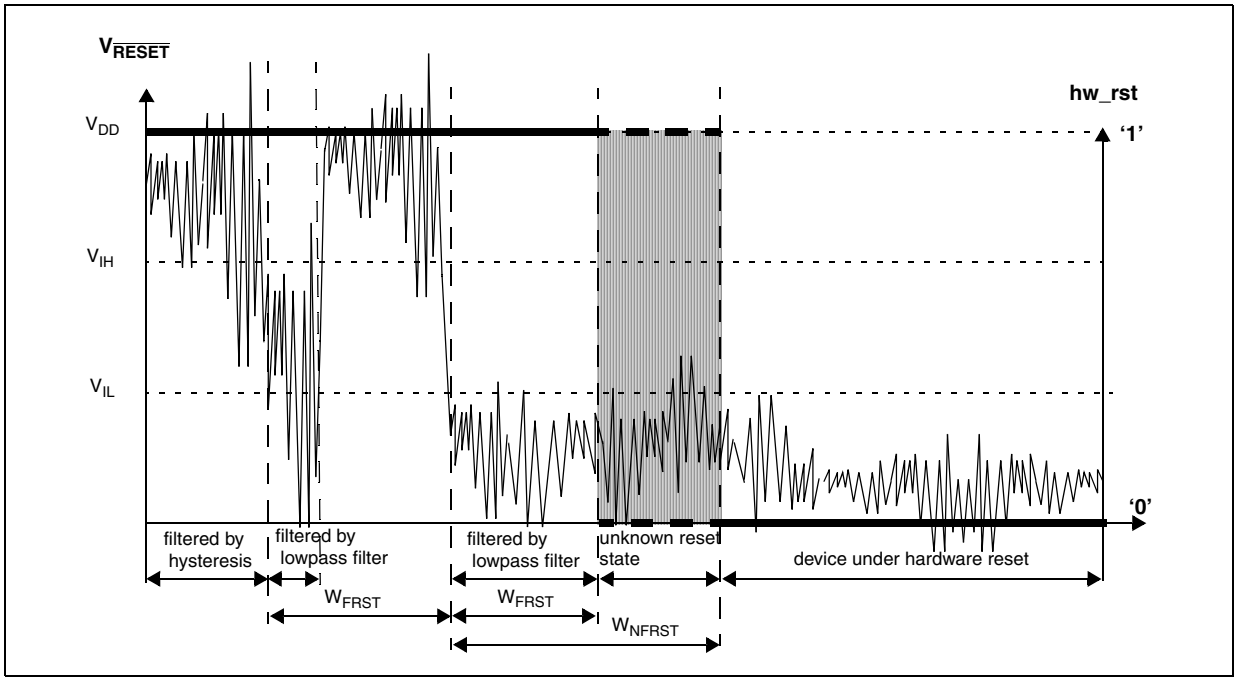


Figure 7. Noise filtering on reset signal

Table 21. Reset electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
V_{IH}	SR	P	Input High Level CMOS (Schmitt Trigger)	—	$0.65V_{DD}$	—	V_{DD} + 0.4	V

3.8 Power management electrical characteristics

3.8.1 Voltage regulator electrical characteristics

The device implements an internal voltage regulator to generate the low voltage core supply V_{DD_LV} from the high voltage ballast supply V_{DD_BV}. The regulator itself is supplied by the common I/O supply V_{DD}. The following supplies are involved:

- HV: High voltage external power supply for voltage regulator module. This must be provided externally through V_{DD} power pin.
- BV: High voltage external power supply for internal ballast module. This must be provided externally through V_{DD_BV} power pin. Voltage values should be aligned with V_{DD}.
- LV: Low voltage internal power supply for core, FMPLL and Flash digital logic. This is generated by the internal voltage regulator but provided outside to connect stability capacitor. It is further split into four main domains to ensure noise isolation between critical LV modules within the device:
  - LV_COR: Low voltage supply for the core. It is also used to provide supply for FMPLL through double bonding.
  - LV_CFLA: Low voltage supply for code Flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
  - LV_DFLA: Low voltage supply for data Flash module. It is supplied with dedicated ballast and shorted to LV_COR through double bonding.
  - LV_PLL: Low voltage supply for FMPLL. It is shorted to LV_COR through double bonding.

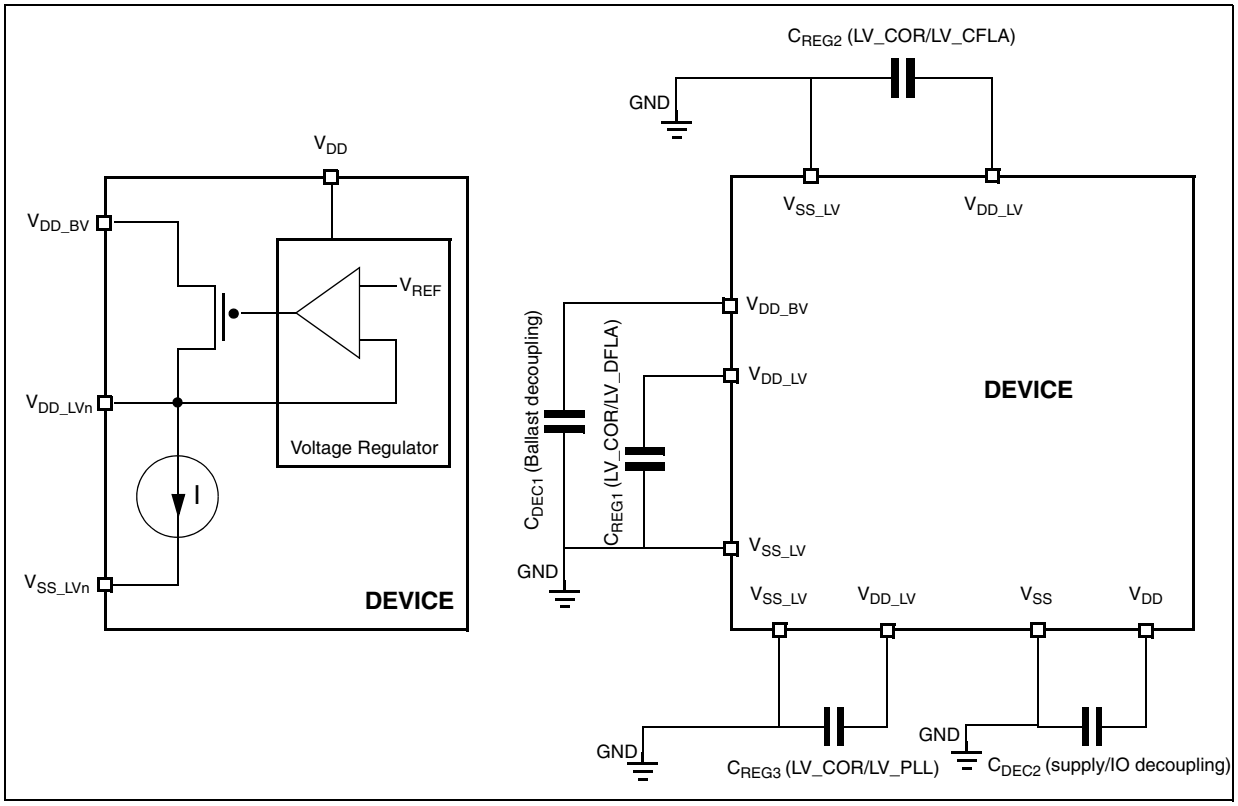


Figure 8. Voltage regulator capacitance connection

The internal voltage regulator requires external capacitance (C_{REGn}) to be connected to the device in order to provide a stable low voltage digital supply to the device. Capacitances should be placed on the board as near as possible to the associated pins. Care should also be taken to limit the serial inductance of the board to less than 5 nH.

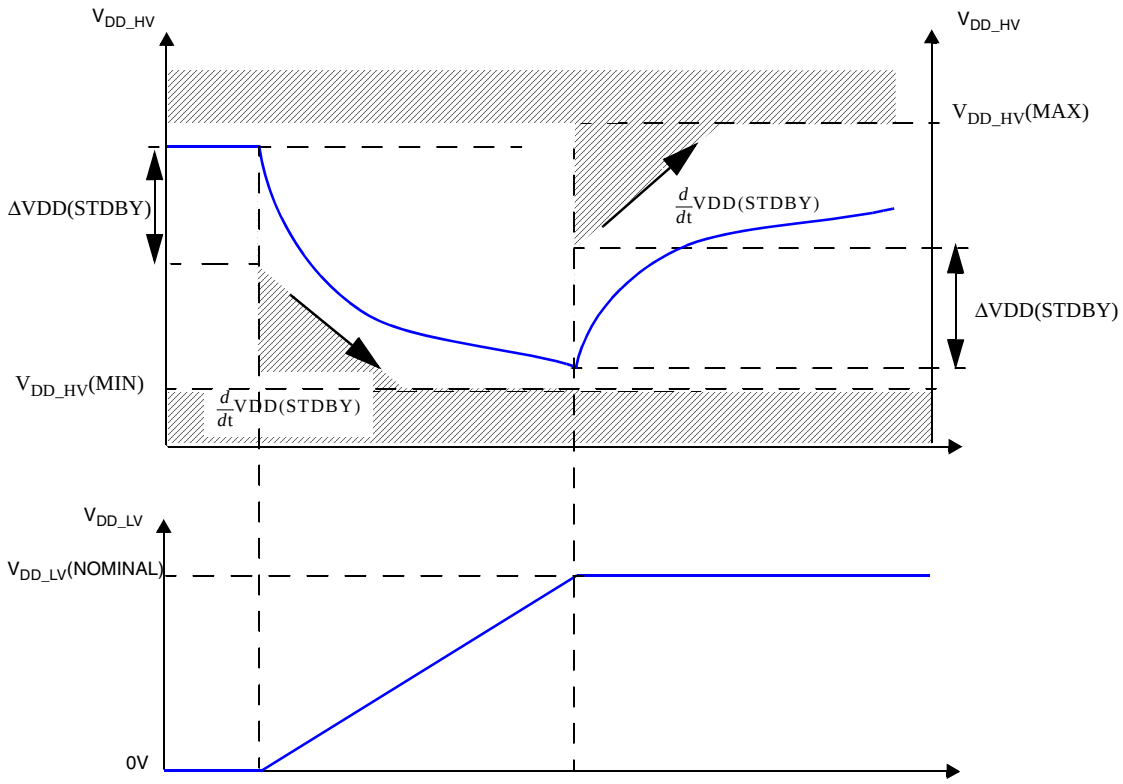


Figure 10. V_{DD} and V_{DD_BV} supply constraints during STANDBY mode exit

Table 22. Voltage regulator electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
C_{REGn}	SR	—	Internal voltage regulator external capacitance	—	200	—	500	nF
R_{REG}	SR	—	Stability capacitor equivalent serial resistance	—	—	—	0.2	Ω
C_{DEC1}	SR	—	Decoupling capacitance[2] ballast	V_{DD_BV}/V_{SS_LV} pair: V_{DD_BV} = 4.5 V to 5.5 V	100[3]	470[4]	—	nF
				V_{DD_BV}/V_{SS_LV} pair: V_{DD_BV} = 3 V to 3.6 V	400		—	
C_{DEC2}	SR	—	Decoupling capacitance regulator supply	V_{DD}/V_{SS} pair	10	100	—	nF
V_{MREG}	CC	P	Main regulator output voltage	Before exiting from reset	—	1.32	—	V
				After trimming	1.15	1.28	1.32	
I_{MREG}	SR	—	Main regulator current provided to V_{DD_LV} domain	—	—	—	150	mA

[4] Higher current may be sunk by device during power-up and standby exit. Please refer to inrush current in Table 22.

[5] RUN current measured with typical application with accesses on both Flash and RAM.

[6] Only for the “P” classification: Data and Code Flash in Normal Power. Code fetched from RAM: Serial IPs CAN and LIN in loop back mode, DSPI as Master, PLL as system clock (4 x Multiplier) peripherals on (eMIOS/CTU/ADC) and running at max frequency, periodic SW/WDG timer reset enabled.

[7] Data Flash Power Down. Code Flash in Low Power. SIRC 128 kHz and FIRC 16 MHz on. 10 MHz XTAL clock. FlexCAN: instances: 0, 1, 2 ON (clocked but not reception or transmission), instances: 4, 5, 6 clocks gated. LINFlex: instances: 0, 1, 2 ON (clocked but not reception or transmission), instance: 3 to 9 clocks gated. eMIOS: instance: 0 ON (16 channels on PA[0]–PA[11] and PC[12]–PC[15]) with PWM 20 kHz, instance: 1 clock gated. DSPI: instance: 0 (clocked but no communication), instance: 1 to 5 clocks gated. RTC/API ON. PIT ON. STM ON. ADC1 OFF. ADC0 ON but no conversion except two analog watchdogs.

[8] Only for the “P” classification: No clock, FIRC 16 MHz off, SIRC 128 kHz on, PLL off, HPvreg off, ULPVreg/LPVreg on. All possible peripherals off and clock gated. Flash in power down mode.

[9] Only for the “P” classification: ULPreg on, HP/LPVreg off, 32 KB RAM on, device configured for minimum consumption, all possible modules switched off.

[10] ULPreg on, HP/LPVreg off, 8 KB RAM on, device configured for minimum consumption, all possible modules switched off.

3.10 Flash memory electrical characteristics

3.10.1 Program/erase characteristics

Table 25 shows the program and erase characteristics.

Table 25. Program and erase specifications

Symbol		C	Parameter	Conditions	Value				Unit
					Min	Typ[1]	Initial max[2]	Max[3]	
$T_{dwprogram}$	CC	C	Double word (64 bits) program time[4]	Code Flash	—	18	50	500	µs
				Data Flash		22			
$T_{16Kpperase}$			16 KB block preprogram and erase time	Code Flash	—	200	500	5000	ms
				Data Flash		300			
$T_{32Kpperase}$			32 KB block preprogram and erase time	Code Flash	—	300	600	5000	ms
				Data Flash		400			
$T_{32Kpperase}$			32 KB block preprogram and erase time for sector B0F4	Code Flash	—	600	1200	10000	ms
$T_{128Kpperase}$			128 KB block preprogram and erase time	Code Flash	—	600	1300	7500	ms
				Data Flash		800			
$T_{128Kpperase}$			128 KB block preprogram and erase time for sector B0F5	Code Flash	—	1200	2600	15000	ms
T_{eslat}		D	Erase Suspend Latency	—	—	—	30	30	µs
T_{ESRT}		C	Erase Suspend Request Rate	Code Flash	20	—	—	—	ms
				Data Flash	10	—	—	—	

Table 31. ESD absolute maximum ratings[1,2]

Symbol	Ratings	Conditions	Class	Max value[3]	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human Body Model)	T_A = 25 °C conforming to AEC-Q100-002	H1C	2000	V
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine Model)	T_A = 25 °C conforming to AEC-Q100-003	M2	200	
$V_{ESD(CDM)}$	Electrostatic discharge voltage (Charged Device Model)	T_A = 25 °C conforming to AEC-Q100-011	C3A	500	
				750 (corners)	

1 All ESD testing is in conformity with CDF-AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits.

2 A device will be defined as a failure if after exposure to ESD pulses the device no longer meets the device specification requirements. Complete DC parametric and functional testing shall be performed per applicable device specification at room temperature followed by hot temperature, unless specified otherwise in the device specification.

3 Data based on characterization results, not tested in production

3.11.3.2 Static latch-up (LU)

Two complementary static tests are required on six parts to assess the latch-up performance:

- A supply overvoltage is applied to each power supply pin.
- A current injection is applied to each input, output and configurable I/O pin.

These tests are compliant with the EIA/JESD 78 IC latch-up standard.

Table 32. Latch-up results

Symbol	Parameter	Conditions	Class
LU	Static latch-up class	T_A = 125 °C conforming to JESD 78	II level A

3.12 Fast external crystal oscillator (4 to 16 MHz) electrical characteristics

The device provides an oscillator/resonator driver. Figure 12 describes a simple model of the internal oscillator driver and provides an example of a connection for an oscillator or a resonator.

Table 33 provides the parameter description of 4 MHz to 16 MHz crystals used for the design simulations.

Table 34. Fast external crystal oscillator (4 to 16 MHz) electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
$T_{FXOSCSU}$	CC	T	Fast external crystal oscillator start-up time	f_{OSC} = 4 MHz, OSCILLATOR_MARGIN = 0	—	—	6	ms
				f_{OSC} = 16 MHz, OSCILLATOR_MARGIN = 1	—	—	1.8	
V_{IH}	SR	P	Input high level CMOS (Schmitt Trigger)	Oscillator bypass mode	$0.65V_{DD}$	—	V_{DD} + 0.4	V
V_{IL}	SR	P	Input low level CMOS (Schmitt Trigger)	Oscillator bypass mode	–0.4	—	$0.35V_{DD}$	V

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified

2 Stated values take into account only analog module consumption but not the digital contributor (clock tree and enabled peripherals).

3.13 Slow external crystal oscillator (32 kHz) electrical characteristics

The device provides a low power oscillator/resonator driver.

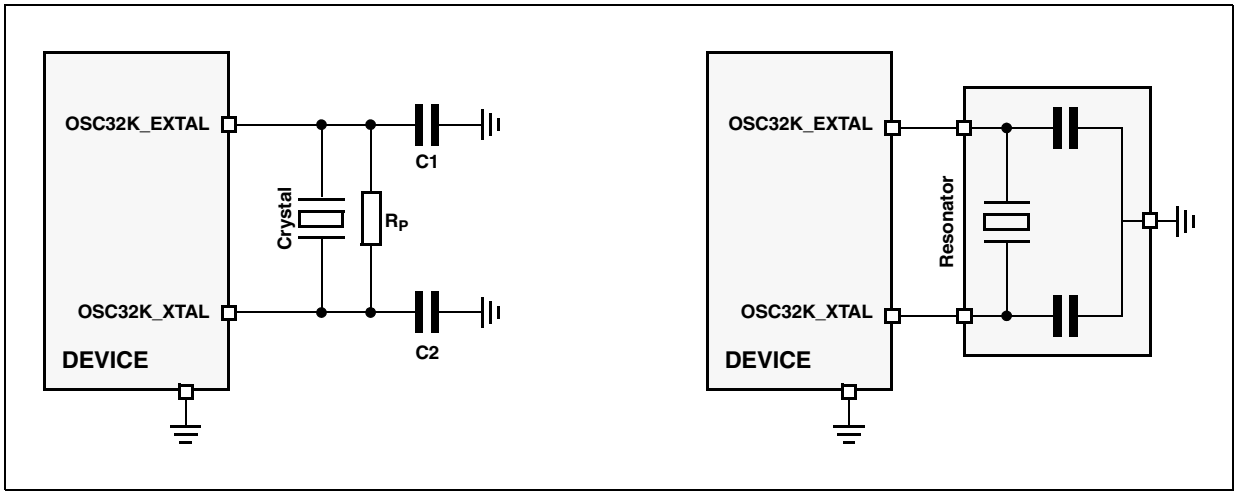


Figure 14. Crystal oscillator and resonator connection scheme

NOTE

OSC32K_XTAL/OSC32K_EXTAL must not be directly used to drive external circuits.

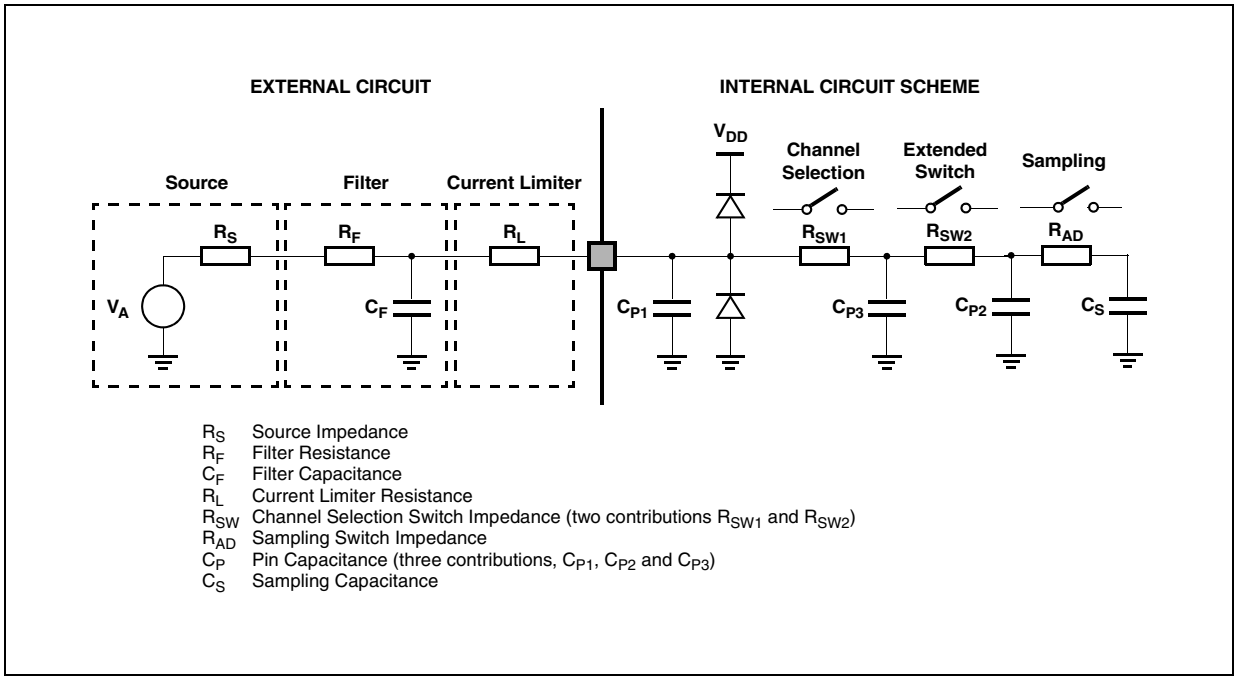


Figure 19. Input equivalent circuit (extended channels)

A second aspect involving the capacitance network shall be considered. Assuming the three capacitances C_F, C_{P1} and C_{P2} are initially charged at the source voltage V_A (refer to the equivalent circuit reported in Figure 18): A charge sharing phenomenon is installed when the sampling phase is started (A/D switch close).

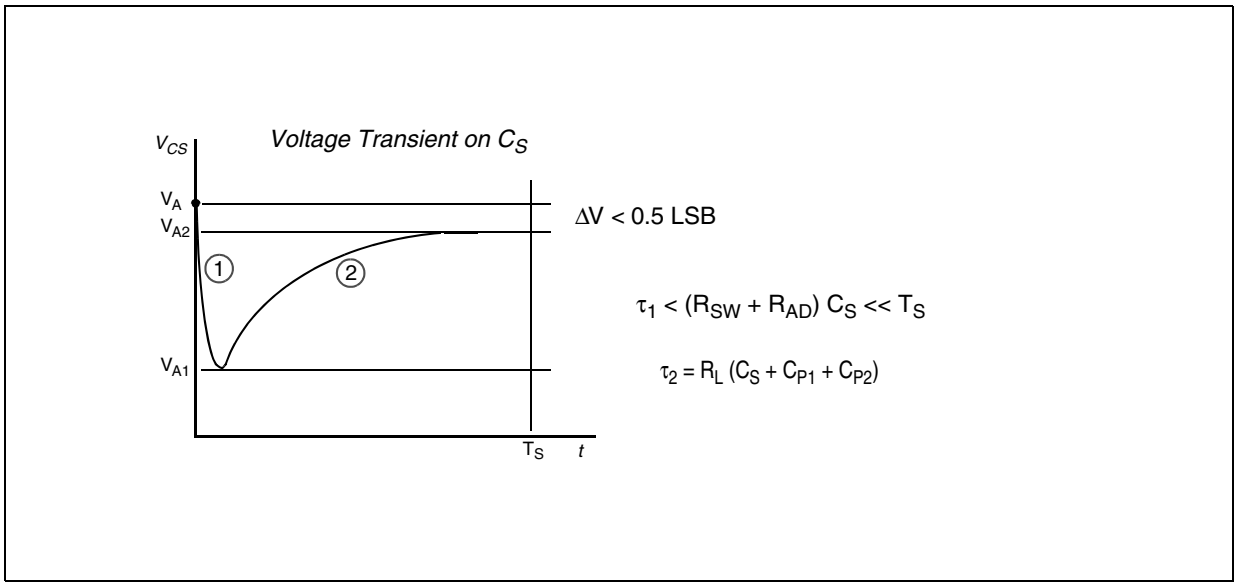


Figure 20. Transient behavior during sampling phase

In particular two different transient periods can be distinguished:

1. A first and quick charge transfer from the internal capacitance C_{P1} and C_{P2} to the sampling capacitance C_S occurs (C_S is supposed initially completely discharged): considering a worst case (since the time constant in reality would be faster) in which C_{P2} is reported in parallel to C_{P1} (call $C_P = C_{P1} + C_{P2}$), the two capacitances C_P and C_S are in series, and the time constant is

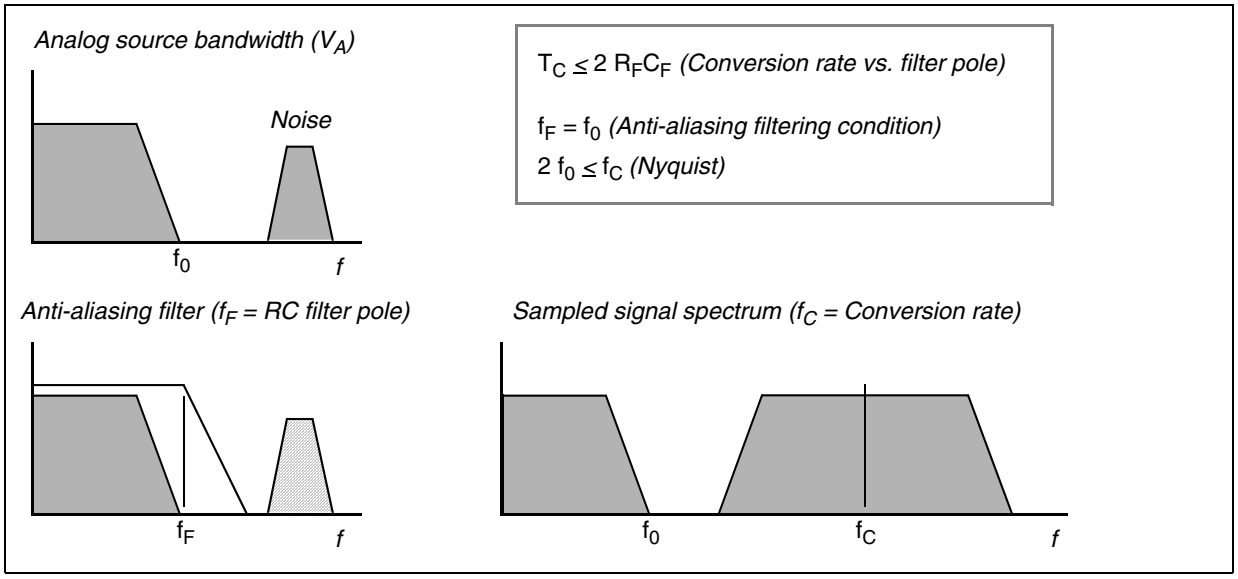


Figure 21. Spectral representation of input signal

Calling f_0 the bandwidth of the source signal (and as a consequence the cut-off frequency of the antialiasing filter, f_F), according to the Nyquist theorem the conversion rate f_C must be at least $2f_0$; it means that the constant time of the filter is greater than or at least equal to twice the conversion period (T_C). Again the conversion period T_C is longer than the sampling time T_S, which is just a portion of it, even when fixed channel continuous conversion mode is selected (fastest conversion rate at a specific channel): in conclusion it is evident that the time constant of the filter $R_F C_F$ is definitively much higher than the sampling time T_S, so the charge level on C_S cannot be modified by the analog signal source during the time in which the sampling switch is closed.

The considerations above lead to impose new constraints on the external circuit, to reduce the accuracy error due to the voltage drop on C_S; from the two charge balance equations above, it is simple to derive Equation 11 between the ideal and real sampled voltage on C_S:

Eqn. 11

$$\frac{V_{A2}}{V_A} = \frac{C_{P1} + C_{P2} + C_F}{C_{P1} + C_{P2} + C_F + C_S}$$

From this formula, in the worst case (when V_A is maximum, that is for instance 5 V), assuming to accept a maximum error of half a count, a constraint is evident on C_F value:

ADC_0 (10-bit) ***Eqn. 12***

$$C_F > 2048 \bullet C_S$$

ADC_1 (12-bit) ***Eqn. 13***

$$C_F > 8192 \bullet C_S$$

Table 41. ADC_0 conversion characteristics (10-bit ADC_0) (continued)

Symbol		C	Parameter	Conditions[1]		Value			Unit
						Min	Typ	Max	
R_{SW1}	CC	D	Internal resistance of analog source	—		—	—	3	kΩ
R_{SW2}	CC	D	Internal resistance of analog source	—		—	—	2	kΩ
R_{AD}	CC	D	Internal resistance of analog source	—		—	—	2	kΩ
I_{INJ}	SR	—	Input current Injection	Current injection on one ADC_0 input, different from the converted one	V_{DD} = 3.3 V ± 10%	–5	—	5	mA
					V_{DD} = 5.0 V ± 10%	–5	—	5	
| INL |	CC	T	Absolute value for integral nonlinearity	No overload		—	0.5	1.5	LSB
| DNL |	CC	T	Absolute differential nonlinearity	No overload		—	0.5	1.0	LSB
| OFS |	CC	T	Absolute offset error	—		—	0.5	—	LSB
| GNE |	CC	T	Absolute gain error	—		—	0.6	—	LSB
TUEP	CC	P	Total unadjusted error[7] for precise channels, input only pins	Without current injection		–2	0.6	2	LSB
		T		With current injection		–3	—	3	
TUEX	CC	T	Total unadjusted error[7] for extended channel	Without current injection		–3	1	3	LSB
		T		With current injection		–4		4	

1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

2 Analog and digital V_{SS} **must** be common (to be tied together externally).

3 V_{AINx} may exceed V_{SS_ADC0} and V_{DD_ADC0} limits, remaining on absolute maximum ratings, but the results of the conversion will be clamped respectively to 0x000 or 0x3FF.

4 Duty cycle is ensured by using system clock without prescaling. When ADCLKSEL = 0, the duty cycle is ensured by internal divider by 2.

5 During the sample time the input capacitance C_S can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_{ADC0_S}. After the end of the sample time t_{ADC0_S}, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_{ADC0_S} depend on programming.

6 This parameter does not include the sample time t_{ADC0_S}, but only the time for determining the digital result and the time to load the result's register with the conversion result.

7 Total Unadjusted Error: The maximum error that occurs without adjusting Offset and Gain errors. This error is a combination of Offset, Gain and Integral Linearity errors.

1 Operating conditions: C_{out} = 10 to 50 pF, $Slew_{IN}$ = 3.5 to 15 ns.

2 For DSPI4, if SOUT is mapped to a SLOW pad while SCK is mapped to a MEDIUM pad (or vice versa), the minimum cycle time for SCK should be calculated based on the rise and fall times of the SLOW pad. For MTFE=1, SOUT must not be mapped to a SLOW pad while SCK is mapped to a MEDIUM pad.

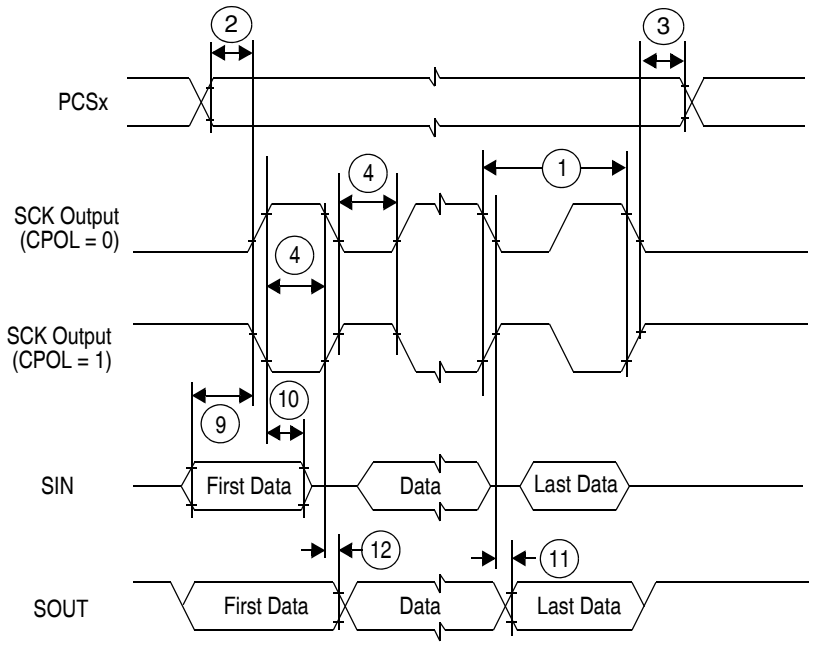
3 The t_{CSC} delay value is configurable through a register. When configuring t_{CSC} (using PCSSCK and CSSCK fields in DSPI_CTAR*x* registers), delay between internal CS and internal SCK must be higher than Δt_{CSC} to ensure positive t_{CSCext}.

4 The t_{ASC} delay value is configurable through a register. When configuring t_{ASC} (using PASC and ASC fields in DSPI_CTAR*x* registers), delay between internal CS and internal SCK must be higher than Δt_{ASC} to ensure positive t_{ASCext}.

5 For DSPI*x*_CTAR*n*[PCSSCK] = 11.

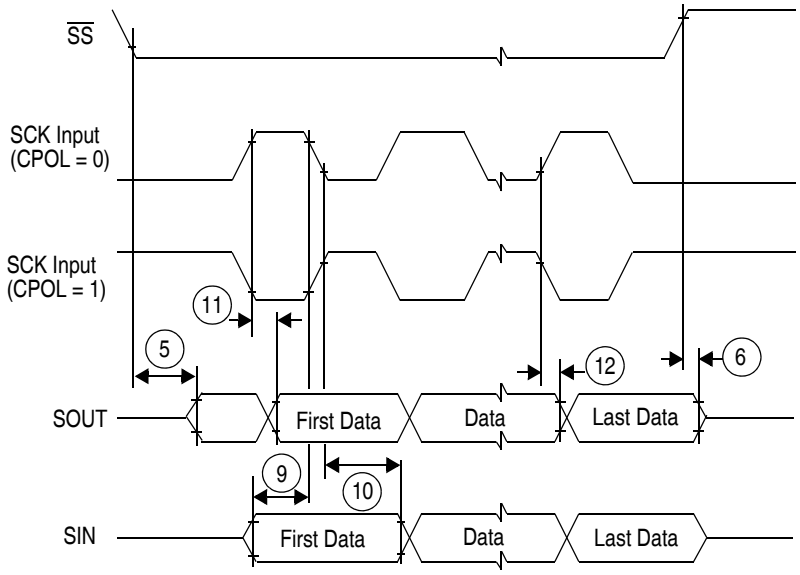
6 This delay value corresponds to SMPL_PT = 00b which is bit field 9 and 8 of DSPI_MCR register.

7 SCK and SOUT are configured as MEDIUM pad.



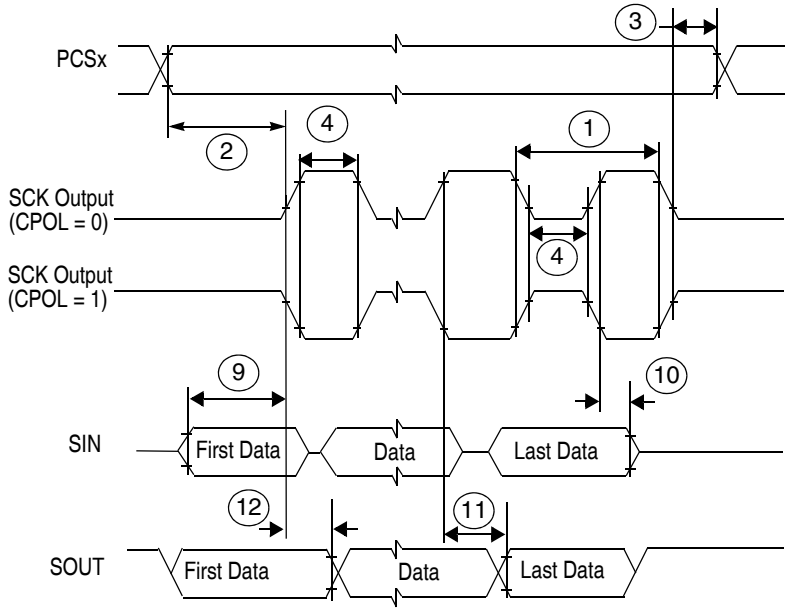
Note: Numbers shown reference Table 44.

Figure 23. DSPI classic SPI timing — master, CPHA = 0



Note: Numbers shown reference Table 44.

Figure 26. DSPI classic SPI timing — slave, CPHA = 1



Note: Numbers shown reference Table 44.

Figure 27. DSPI modified transfer format timing — master, CPHA = 0